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said first electrode layer including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group consisting of Ni, Pd and Co, and Ni / Au

said third electrode layer including Au.

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8. (Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group consisting of Ni and Co, and

said third electrode layer including Au.

Please add new claims 12-14 as follows:

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12. The electrode structure according to claim 8, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.

13. An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

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said first electrode layer having a thickness of 10 to 500 nm and including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer having a thickness of 50 nm or more and including at least one selected from a second metal group consisting of Ni, Pd and Co, and

said third electrode layer having a thickness of 50 nm or more and including Au.

14. The electrode structure according to claim 13, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.
